Ordering number : ENA1480A

SANYO Semiconductors
DATA SHEET

An ON Semiconductor Company

TIG062E8 — N-Channel IGBT Light-Controlling Flash Applications

Features

- Low-saturation voltage.
- Low voltage drive (3V).
- Enhansment type.
- Built-in Gate-to-Emitter protection diode.
- Mounting Height 0.9mm, Mounting Area 8.12mm^2.
- dv / dt guarantee*.
- Halogen free compliance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Emitter Voltage	V_{CES}		400	V
Gate-to-Emitter Voltage (DC)	V_{GES}		±6	V
Gate-to-Emitter Voltage (Pulse)	V_{GES}	PW≤1ms	±8	V
Collector Current (Pulse)	$I_{CP}1$	C_M=150μF, V_{GE}=3V	100	A
	$I_{CP}2$	C_M=100μF, V_{GE}=3.3V	130	A
	$I_{CP}3$	C_M=100μF, V_{GE}=4V	150	A
Maximum Collector-to-Emitter dv / dt	dV_{CE} / dt	V_{CE}≤320V, starting Tch=25°C	400	V / μs
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-40 to +150	°C

Marking : ZC

* : Concerning dv / dt (slope of Collector Voltage at the time of Turn-OFF), dv / dt > 400V / μs will be 100% screen-detected in the circuit shown as Fig. 1.

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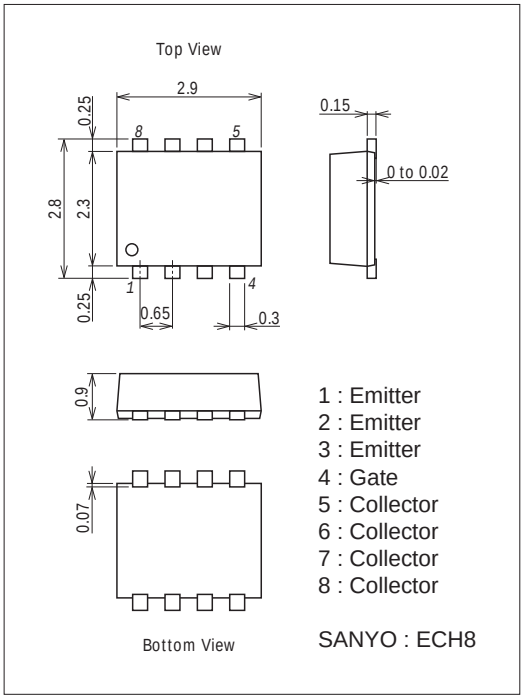
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=2mA, V_{GE}=0V	400			V
Collector-to-Emitter Cutoff Current	I_{CES}	V_{CE}=320V, V_{GE}=0V			10	μA
Gate-to-Emitter Leakage Current	I_{GES}	V_{GE}=±6V, V_{CE}=0V			±10	μA
Gate-to-Emitter Threshold Voltage	V_{GE}(off)	V_{CE}=10V, I_C=1mA	0.4		0.9	V
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=100A, V_{GE}=3V		5	8	V
Input Capacitance	Cies	V_{CE}=10V, f=1MHz		2400		pF
Output Capacitance	Coes	V_{CE}=10V, f=1MHz		32		pF
Reverse Transfer Capacitance	Cres	V_{CE}=10V, f=1MHz		24		pF

Package Dimensions

unit : mm (typ)

7011A-004



Electrical Connection

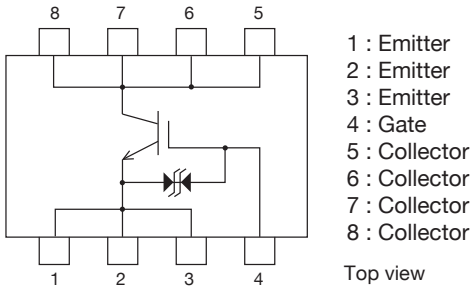
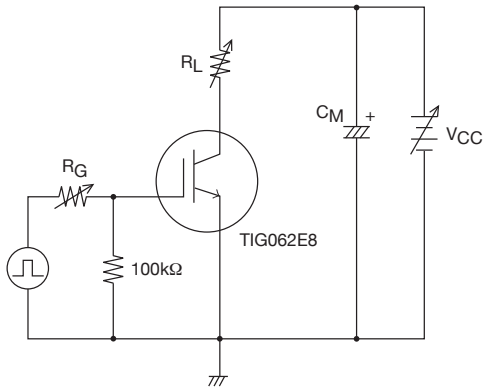
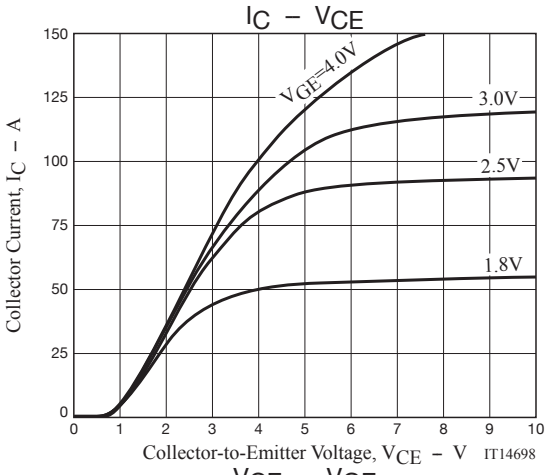


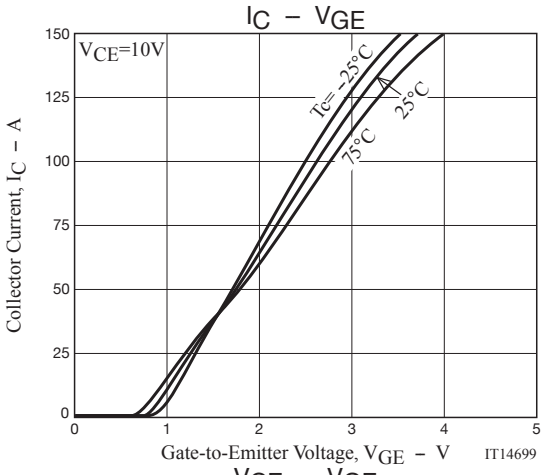
Fig.1 Large Current R Load Switching Circuit

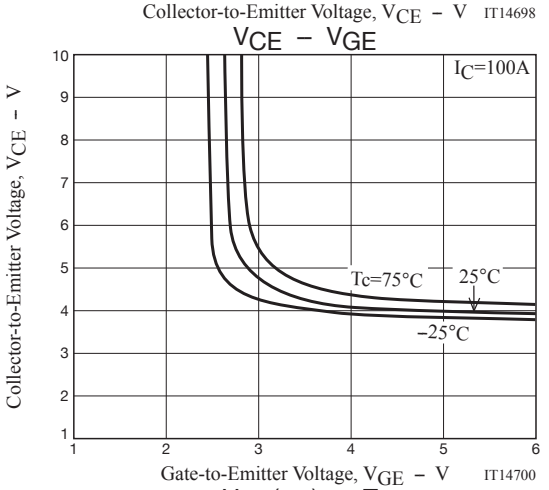


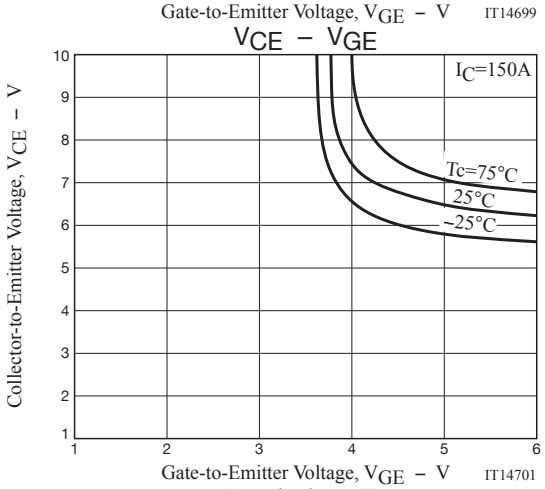
Note1. Gate Series Resistance $R_G \geq 250\Omega$ is recommended for protection purpose at the time of turn OFF. However, if dv / dt ≤ 400V / μs is satisfied at customer's actual set evaluation, $R_G < 250\Omega$ can also be used.

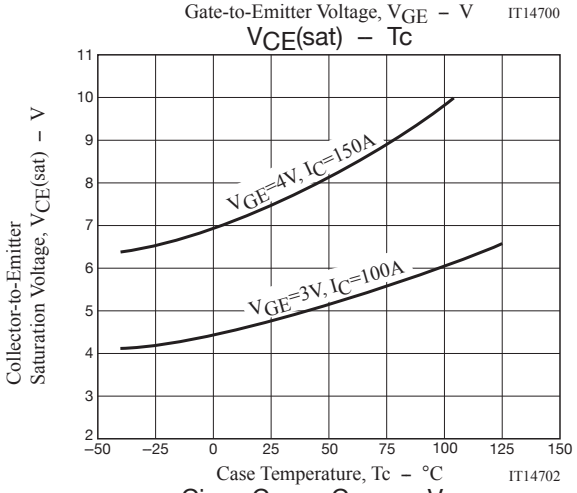
Note2. The collector voltage gradient dv / dt must be smaller than 400V / μs to protect the device when it is turned off.

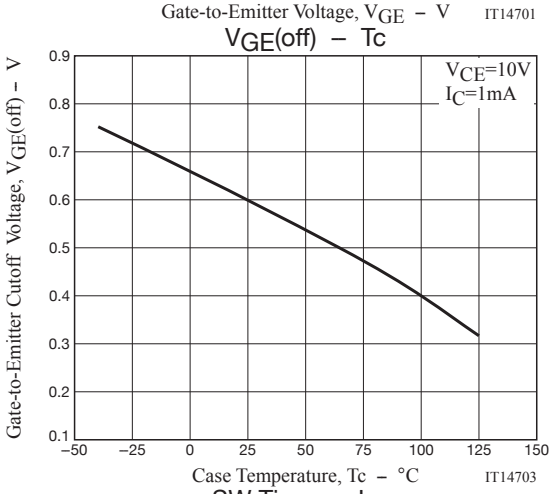


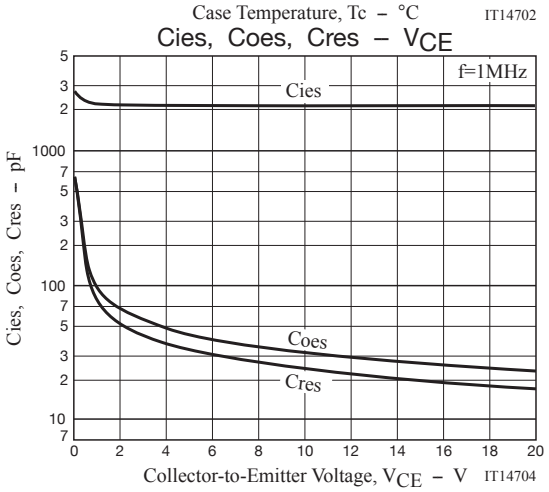


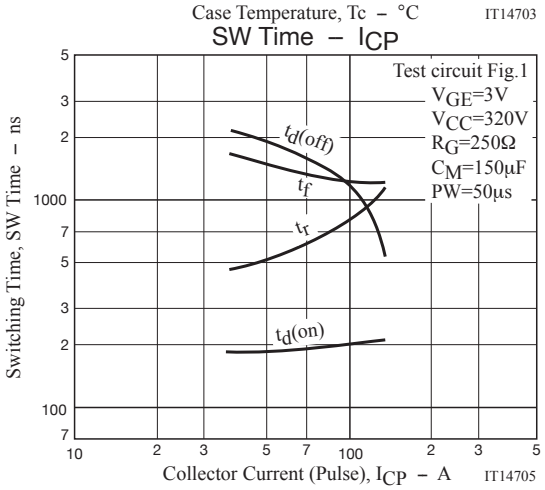




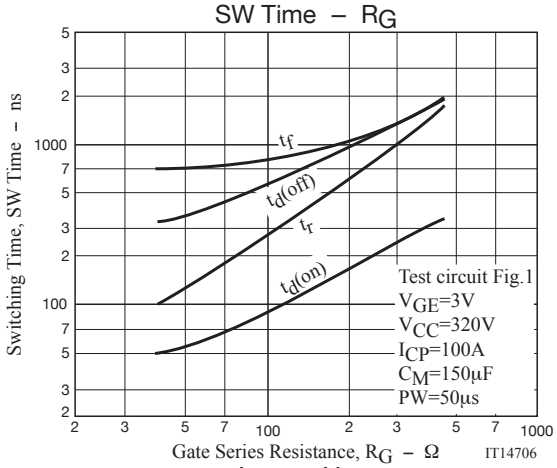




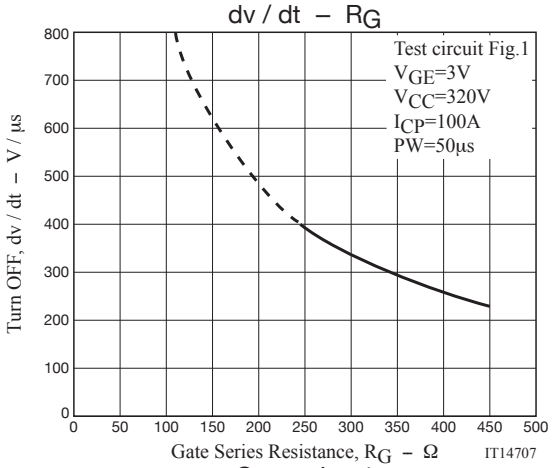




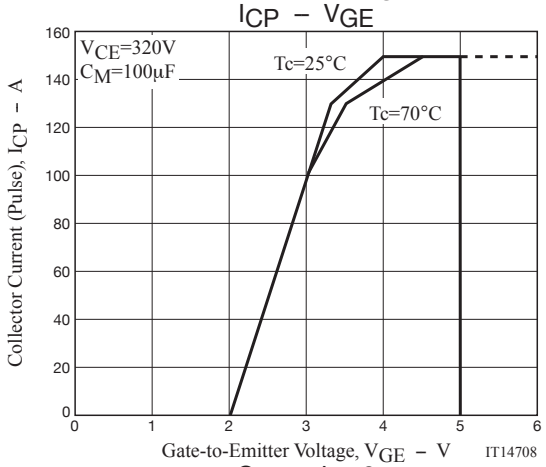
SW Time – R_G



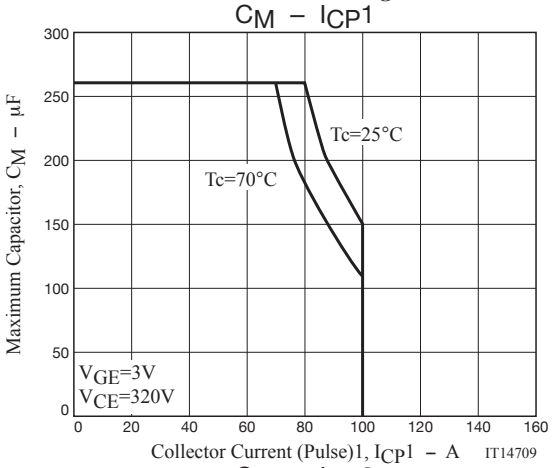
dv / dt – R_G



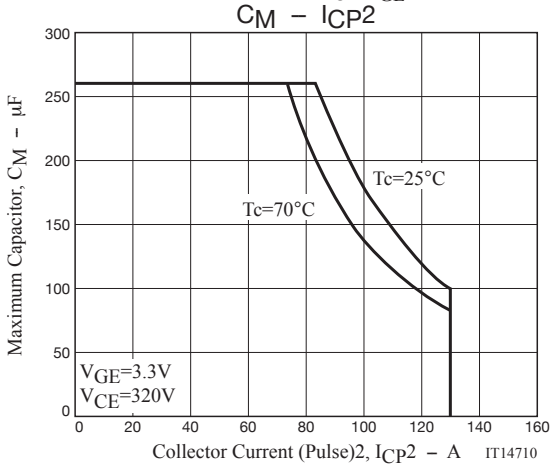
I_{CP} – V_{GE}



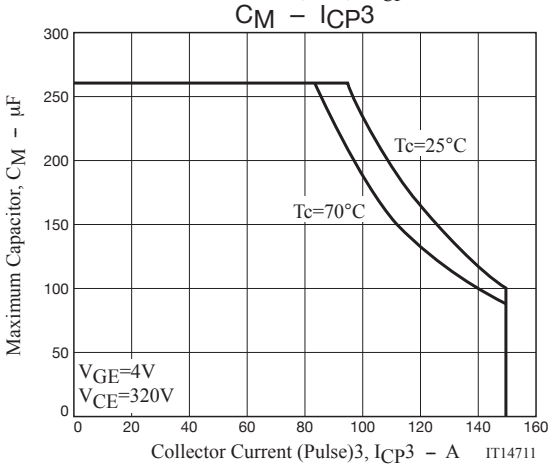
C_M – $I_{CP}1$



C_M – $I_{CP}2$



C_M – $I_{CP}3$



Note : TIG062E8 has protection diode between gate and emitter but handling it requires sufficient care to be taken.

This catalog provides information as of October, 2009. Specifications and information herein are subject to change without notice.